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								U.S	. PATENT	DOCUMENTS	3			· 		
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OTHER DOCUMENTS (including Author, Title, Date, Pertinent Pages, Etc.)																
Sm		Poole, P.J. et al.: "Quantum Well Intermixing For the Realization Of Photonic Integrated Circuits", Proceedings of the SPIE, SPIE, Bellingham, VA, vol. 2613, dated 10-24-95, pages 9-16.														
		Zucker, J.E. et al.: "Large Blueshifting Of INGAAS/INP Quantum-Well Band Gaps By Ion Implantation", Applied Physics Letters, American Institute of Physics, New York, vol. 60, no. 24, dated 6-15-92, pages 3036-3038.														
	Tell, B. et al., "Phosphorus Ion Implantation Induced Intermixing of INGAAS-INP Quantum Well Structures", Applied physics Letters, American Institute of physics, New York, vol. 54, no. 16, dated 4-17-89, pages 1570-1572.															
		Ooi, B.S. et al.: The Application Of The Selective Intermixing In Selected Area (SISA) Technique To The Fabrication Of Photonic Devices In GAAS/ALGAAS Structures", International Journal of Optoelectronics, London, GB., vol. 10, no. 4, dated 7-1-95, pages 257-263.														
		Kupka, R.K. et al.: "Gallium-Implantation-Enhanced Intermicing of Close-Surface GAAS/ALAS/ALGAAS Double-Barrier Quantum Wells", Journal of Applied Physics, American Institute of Physics, New York, vol. 78, no. 4, dated 8-15-95, pages 2355-2361.														
		Paquette, M. et al.: "Blueshifting Of INGAAP/INP Laser Diodes By Low-Energy Ion Implantation", Applied Physics Letters, American Institute of Physics, New York, vol 71, no. 26, dated 12-29-97, pages 3749-3751.														
		Yu, S.J. et al.: "Disordering Of INGASS/INP Superlattice And Fabrication Of Quantum Wires By Focused GA Ion Beam", Journal of Vacuum Science and Technology: Part B, American Institute of Physics, New York, vol. 9, no. 5, dated 9-1-91, pages 2683-2686.														
SM		Co ap	py o	of the	e In	terr	natio	nal Sea	rch Report f	rom a foreign	patent	office	in a c	ounterpa	art foreigr	1
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Application Number 09/916,701

Filling Date July 26, 2001

First Named Inventor Ooi, Boon-Siew

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Examiner Name

Attorney Docket Number

Initials * No	Cite No.1	U.S. Patent Document Kind Code ²	Name of Patentee or Applicant	Date of Publication of Cited Document	Pages, Columns, Lines, Where Relevant		
		Number (if known)	of Cited Document	MM-DD-YYYY	Passages or Relevant Figures Appear		
40	AA	4,511,408	Holonyak, Jr.	04-16-85			
7	AB	4,771,010	Epler,et al.	09-13-88			
	AC	4,802,182	Thornton, et al.	01-31-89	,		
	AD	4,824,798	Burnham, et al.	04-25-89			
	AE	4,830,983	Thornton	05-16-89			
	AF	4,871,690	Holonyak, Jr., et al.	10-03-89			
1	AG	5,031,185	Murakami, et al.	07-09-91			
	AH	5,145,792	Hirata	09-08-92			
	Al	5,238,868	Elman, et al.	08-24-93			
\neg	AJ	5,276,745	Revelli, Jr.	01-04-94	,		
	AK	5,395,793	Charbonneau, et al.	03-07-95			
	AL	5,539,763	Takemi, et al.	07-23-96			
	AM	5,556,804	Nagai	09-17-96			
	AN	5,707,890	Emery, et al.	01-13-98			
SA	AO	6,027,989	Poole, et al.	02-22-00			
-							

FOREIGN PATENT DOCUMENTS								
		For	eign Patent D	ocument	Name of Patentee	Date of Publication of	Pages, Columns, Lines, Where Relevant	
Examiner Initials*		Number ⁴	Kind Code ⁵ (<i>if known</i>)	or Applicant of Cited Document	Cited Document MM-DD-YYYY	Passages or Relevant Figures Appear	T ⁶	
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¹ Unique citation designation number. ² See attached Kinds of U.S. Patent Documents. ³ Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). ⁴ For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. ⁵ Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST. 16 if possible. ⁶ Applicant is to place a check mark here if English language Translation is attached.